2SB560

2006A

PNP/NPN Epitaxial Planar Silicon Transistors

2SD438

Low Frequency Power Amp Applications

©326G

The 2SB560/2SD438 are epitaxial planar transistors for complementary push-p pair having high reverse voltage and low saturation voltage, and suital universal AF power amplifier use.

( ):2SB560

Absolute Maximum Ratings at Ta=25°C

			unit
Collector to Base Voltage	V_{CBO}	(-)100	V
Collector to Emitter Voltage	V_{CEO}	(-)80	V
Emitter to Base Voltage	V_{EBO}	(-)5	V
Collector Current	I_C	(-)0.7	A
Peak Collector Current	i_{cp}	(-)1.0	A
Collector Dissipation	P_C	900	mW
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	-55 to +150	°C

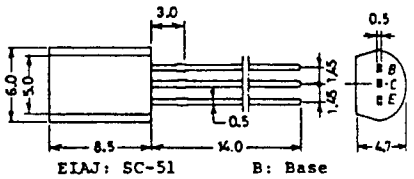
Electrical Characteristics at Ta=25°C

			min	typ	max
Collector Cutoff Current	I_{CBO}	V_{CB}=(-)20V,I_E=0			(-)1.0
Emitter Cutoff Current	I_{EBO}	V_{EB}=(-)4V,I_C=0			(-)1.0
DC Current Gain	$h_{FE}(1)$	V_{CE}=(-)5V,I_C=(-)50mA	60*		560*
	$h_{FE}(2)$	V_{CE}=(-)5V,I_C=(-)0.5A	30		
Gain Bandwidth Product	f_T	V_{CE}=(-)10V,I_C=(-)50mA		100	
Output Capacitance	c_{ob}	V_{CE}=(-)10V,f=1MHz		(15) 10	
C-B Breakdown Voltage	$V_{(BR)CBO}$	I_C=10uA	(-)100		
C-E Breakdown Voltage	$V_{(BR)CEO}$	I_C=1mA,R_{BE}=∞	(-)80		
E-B Breakdown Voltage	$V_{(BR)EBO}$	I_C=(-)10uA,I_C=0	(-)5		
C-E Saturation Voltage	$V_{CE(sat)}$	I_C=(-)500mA,I_B=(-)50mA		(-0.3) 0.2	(-0.8) 0.6
B-E Saturation Voltage	$V_{BE(sat)}$	I_C=(-)500mA,I_B=(-)50mA		(-)0.85	(-)1.2

* The 2SB560/2SD438 are classified by 50mA h_{FE} as follows.

60	D	120	100	E	200	160	F	320	280	G	560

Case Outline 2006A
(unit:mm)



EIAJ: SC-51
SANYO:MP

B: Base
C: Collector
E: Emitter

For details, refer to the description of the 2SD438.